



Thyristor / Diode Modules

SKKH 75/16 E

Features*

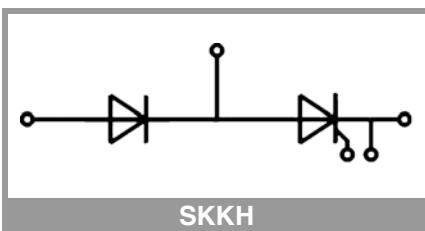
- Heat transfer through aluminium oxide ceramic insulated metal baseplate
- UL recognized, file no. E63532

Typical Applications

- Rectifier for motor drives
- Process control
- Rectifier for power supplies

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
Thyristor / diode			
$I_{F(AV)}/I_{T(AV)}$	$\sin. 180^\circ$ $T_j = 130^\circ\text{C}$	$T_c = 85^\circ\text{C}$ $T_c = 100^\circ\text{C}$	75 57
I_{FSM}/I_{TSM}	$t_p = 10 \text{ ms}$	$T_j = 25^\circ\text{C}$ $T_j = 130^\circ\text{C}$	1500 1200
i^2t	$t_p = 10 \text{ ms}$	$T_j = 25^\circ\text{C}$ $T_j = 130^\circ\text{C}$	11250 7200
V_{RSM}	$T_j = 25^\circ\text{C}$, thyristor, diode		1700
V_{RRM}	$T_j = 25^\circ\text{C}$, thyristor, diode		1600
V_{DRM}	$T_j = 25^\circ\text{C}$, thyristor		1600
$(di/dt)_{cr}$	$T_j = 130^\circ\text{C}$, thyristor		200
$(dv/dt)_{cr}$	$T_j = 130^\circ\text{C}$, thyristor		1000
T_j			-40 ... 130
Module			
T_{stg}			-40 ... 125
V_{isol}	a.c.; 50 Hz; r.m.s.	1 min 1 s	3000 3600

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
Thyristor					
V_T	$T_j = 25^\circ\text{C}$, $I_T = 225 \text{ A}$			1.81	V
$V_{T(TO)}$	$T_j = 130^\circ\text{C}$			0.92	V
r_T	$T_j = 130^\circ\text{C}$			4.6	$\text{m}\Omega$
I_{DD}, I_{RD}	$T_j = 130^\circ\text{C}$, $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$			15	mA
t_{gd}	$T_j = 25^\circ\text{C}$, $I_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$		1		μs
t_{gr}	$V_D = 0.67 * V_{DRM}$		2		μs
t_q	$T_j = 130^\circ\text{C}$		200		μs
I_H	$T_j = 25^\circ\text{C}$			220	mA
I_L	$T_j = 25^\circ\text{C}$, $R_G = 33 \Omega$			550	mA
V_{GT}	$T_j = 25^\circ\text{C}$, d.c.		2.5		V
I_{GT}	$T_j = 25^\circ\text{C}$, d.c.		100		mA
V_{GD}	$T_j = 130^\circ\text{C}$, d.c.			0.25	V
I_{GD}	$T_j = 130^\circ\text{C}$, d.c.			4	mA
$R_{th(j-c)}$	cont., per chip			0.23	K/W
	$\sin. 180^\circ$, per chip			0.30	K/W
	rec. 120° , per chip			0.32	K/W
Diode					
V_F	$T_j = 25^\circ\text{C}$, $I_F = 225 \text{ A}$			1.65	V
V_{FO}	$T_j = 130^\circ\text{C}$			0.85	V
r_F	$T_j = 130^\circ\text{C}$			3.90	$\text{m}\Omega$
I_R	$T_j = 130^\circ\text{C}$, $V_{RD} = V_{RRM}$			1.7	mA
$R_{th(j-c)}$	cont., per chip			0.30	K/W
	$\sin. 180^\circ$, per chip			0.38	K/W
	rec. 120° , per chip			0.40	K/W





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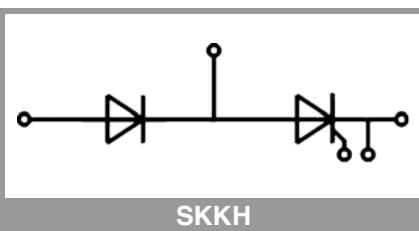
Features*

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Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
Module					
R _{th(c-s)}	thyristor ($\lambda_{grease} = 0.81 \text{ W}/(\text{m}^*\text{K})$)		0.09		K/W
	diode ($\lambda_{grease} = 0.81 \text{ W}/(\text{m}^*\text{K})$)		0.09		K/W
	module ($\lambda_{grease} = 0.81 \text{ W}/(\text{m}^*\text{K})$)		0.05		K/W
M _s	to heatsink M5	4.25	5.75		Nm
M _t	to terminals M5	2.55	3.45		Nm
a			5 * 9.81		m/s ²
w		75			g



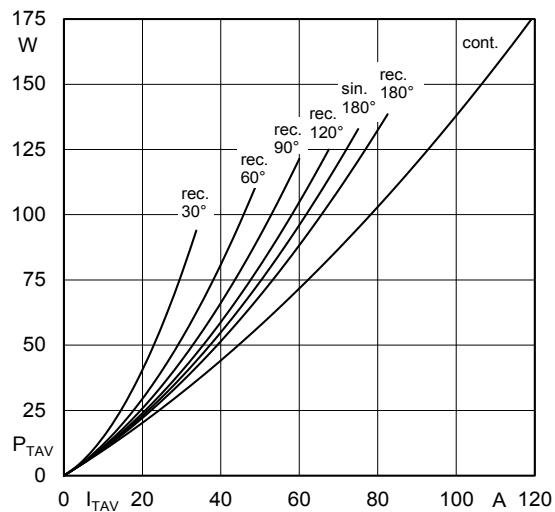


Fig. 1L: Power dissipation per thyristor vs. on-state current

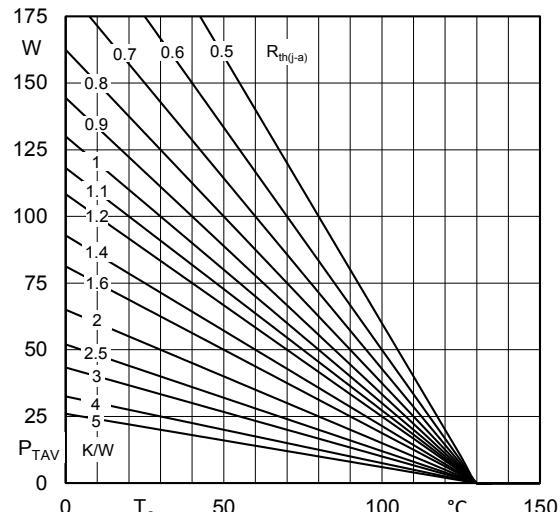


Fig. 1R: Max. power dissipation per thyristor vs. ambient temperature

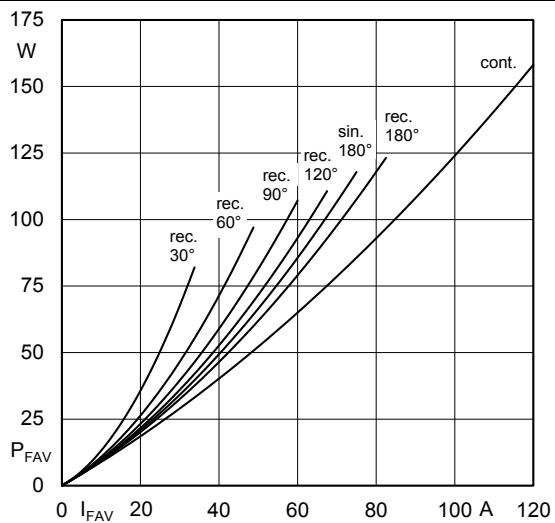


Fig. 2L: Power dissipation per diode vs. forward current

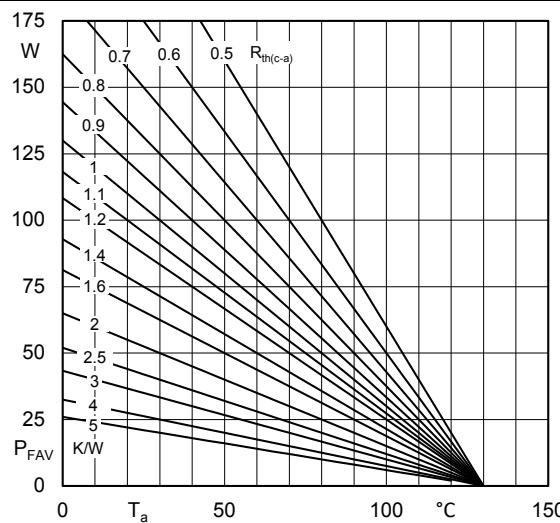


Fig. 2R: Max power dissipation per diode vs. ambient temperature

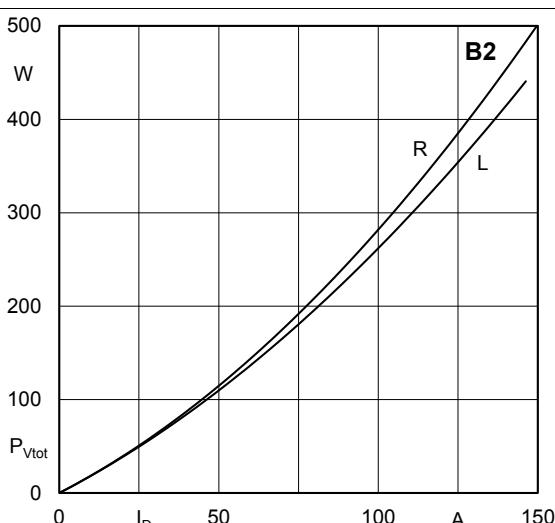


Fig. 3L: Max. power dissipation of two modules vs. direct current

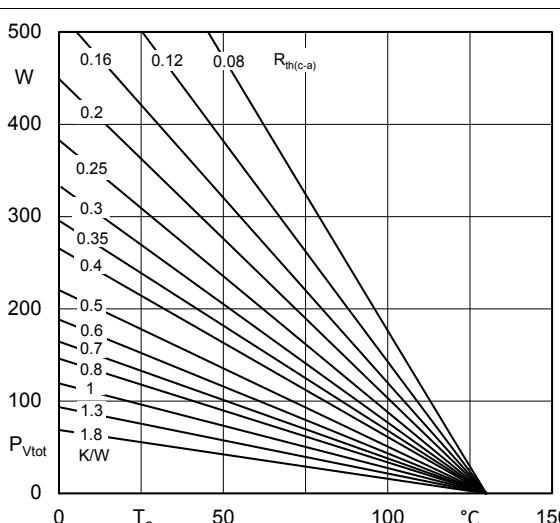


Fig. 3R: Max. power dissipation of two modules vs. ambient temperature

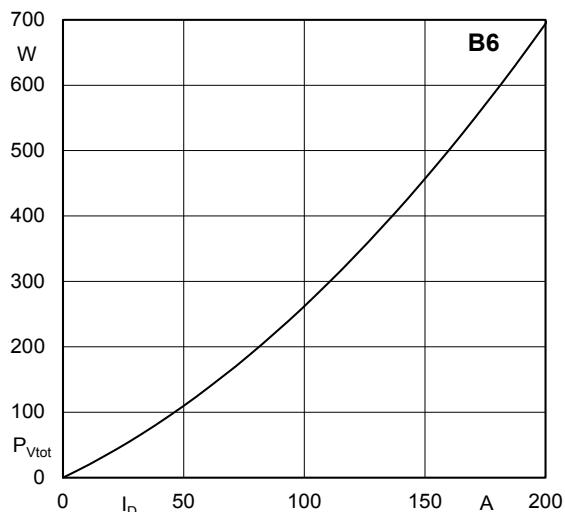


Fig. 4L: Max. power dissipation of three modules vs. direct current

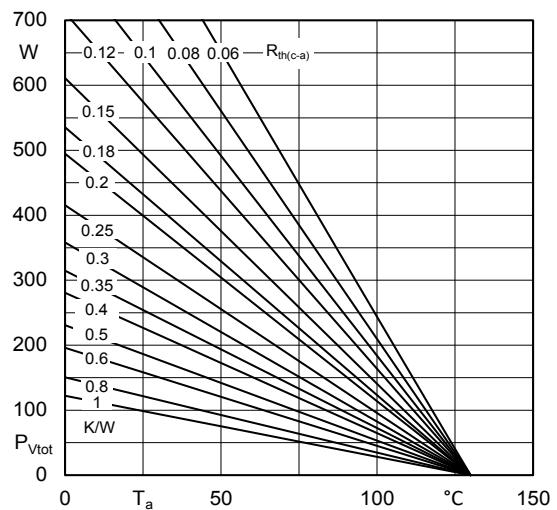


Fig. 4R: Max. power dissipation of three modules vs. ambient temperature

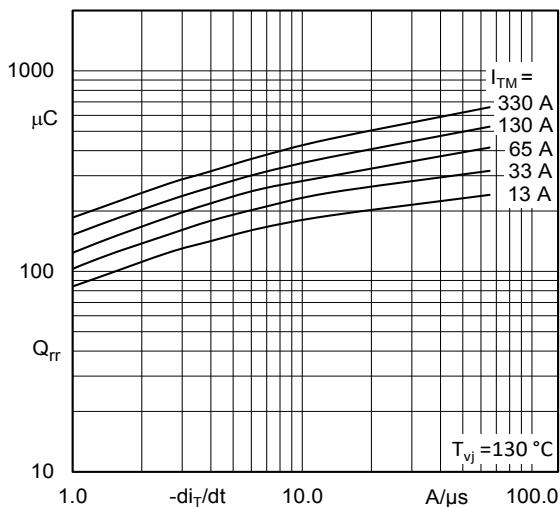


Fig. 5: Recovered charge vs. current decrease

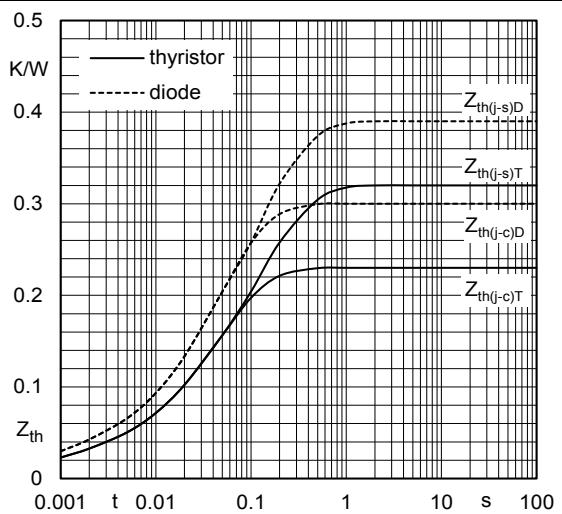


Fig. 6: Transient thermal impedance vs. time

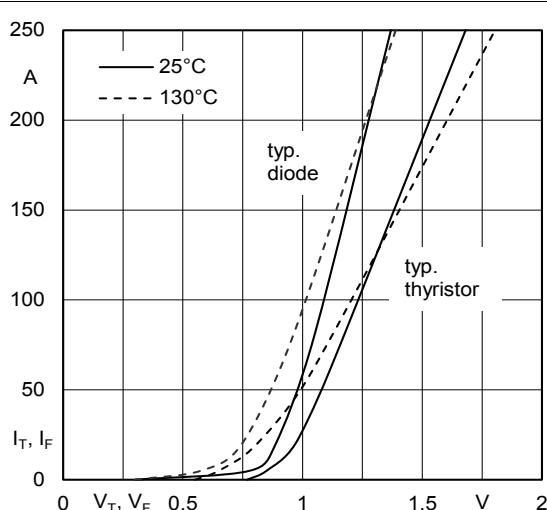


Fig. 7: On-state characteristics

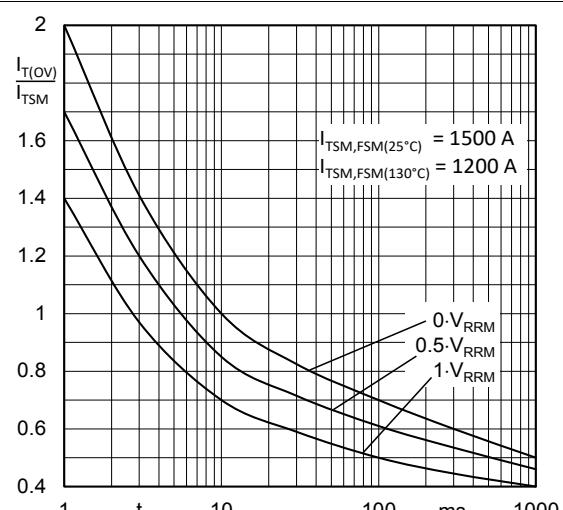
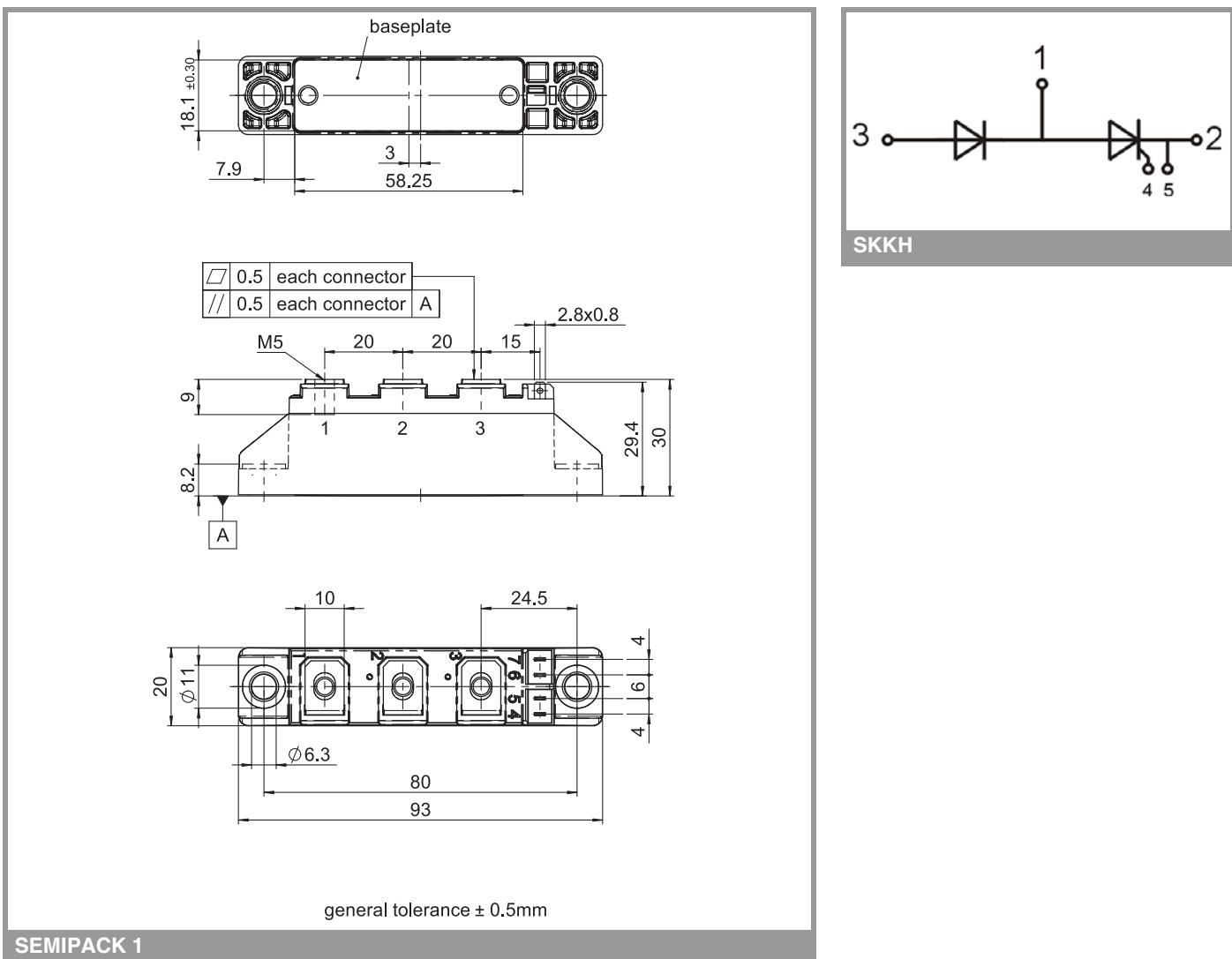
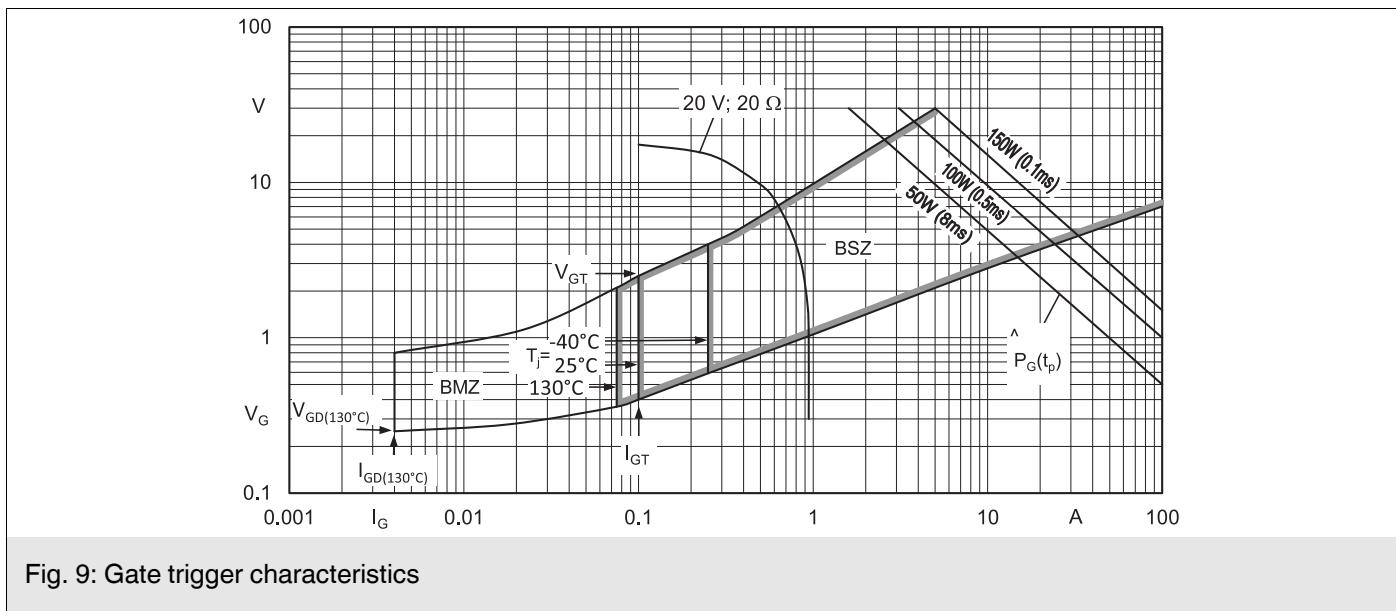


Fig. 8: Surge overload current vs. time



IMPORTANT INFORMATION AND WARNINGS

This is an electrostatic discharge sensitive device (ESDS) according to international standard IEC 61340.

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